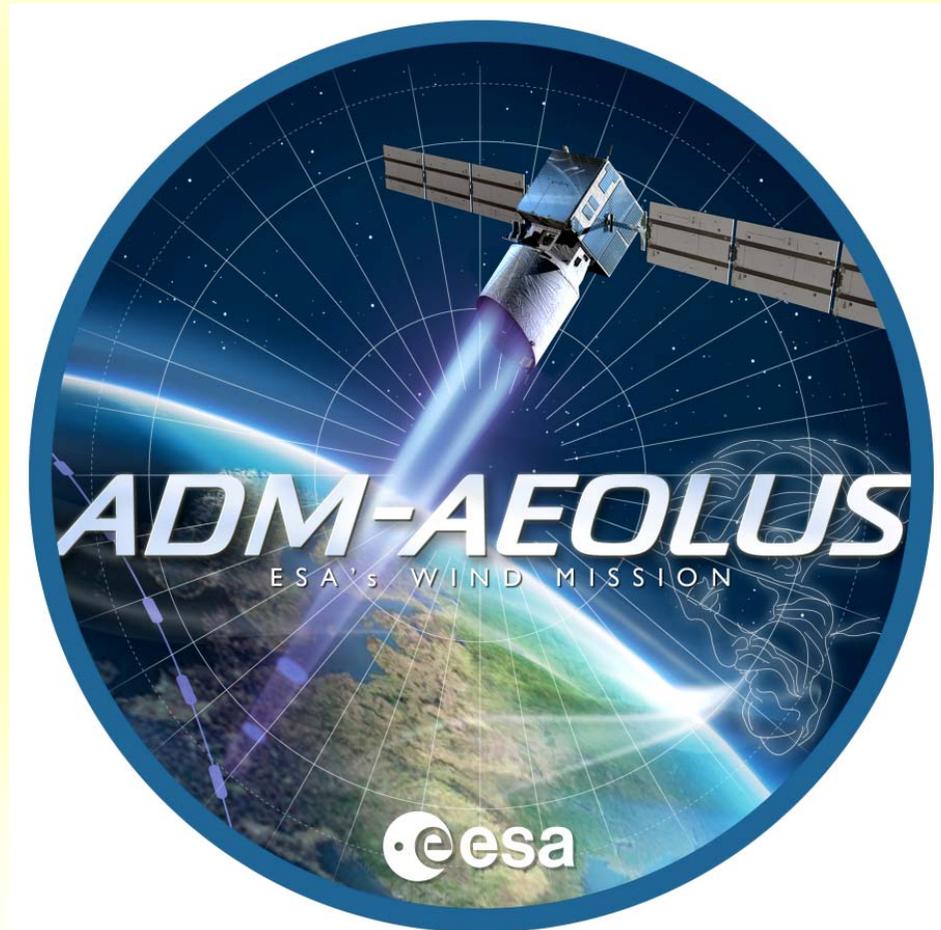
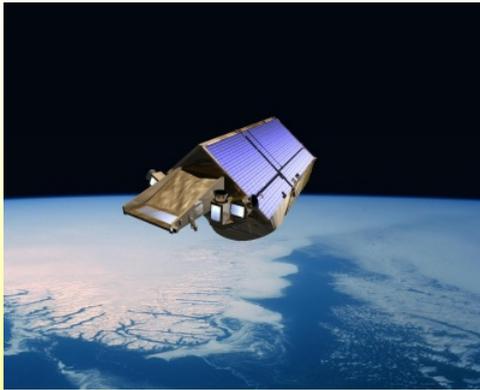


Assessment Test Programme on the ALADIN CW Pump Laser Diodes



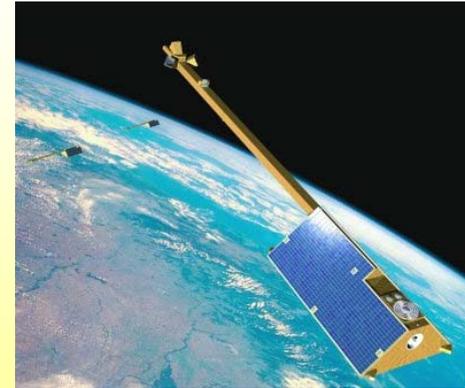
Selected Earth Explorers



CRYOSAT - 2005



SMOS - 2007



SWARM - 2009



GOCE - 2006



ADM-Aeolus - 2008



EarthCARE - 2012

- Goal: risk reduction before committing to full development of instruments approved for flight

- How?

- Design, manufacture and test critical subsystems

- Space-representative build standards

- Demonstrate instrument performances

- Realisation of ground/airborne instrument

- Atmospheric **LA**ser **D**oppler **IN**strument (ALADIN) Pre-Development Programme (start 2000):

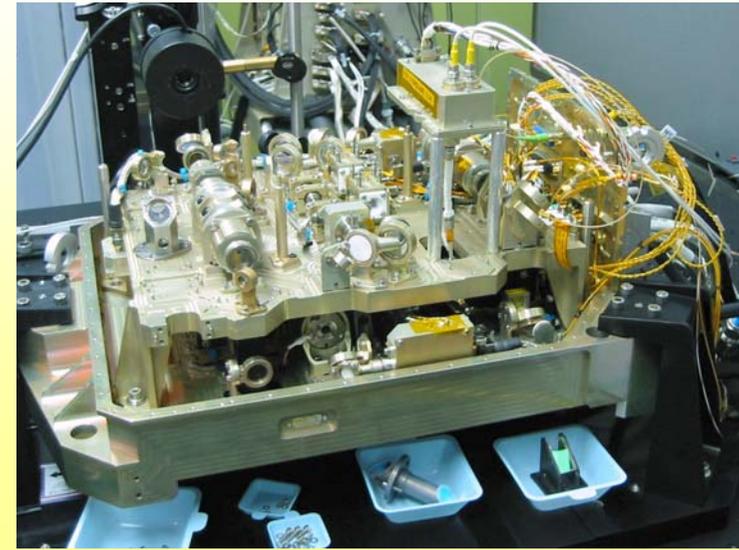
- Pre-Development Model of receiver

- 2 parallel contracts on laser transmitter

- 4 parallel contracts on pump laser diodes assessment: CW & QCW

- Studies of specific technology improvement

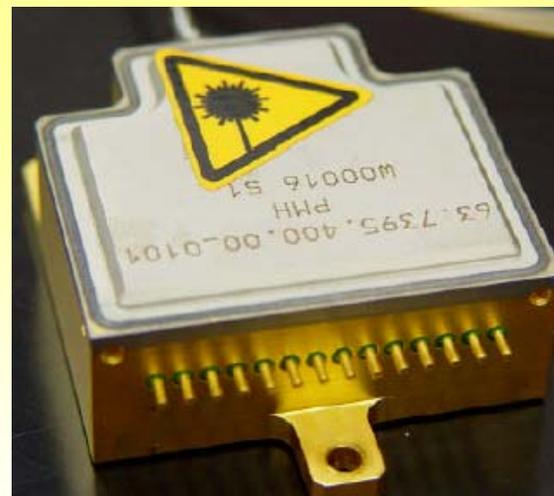
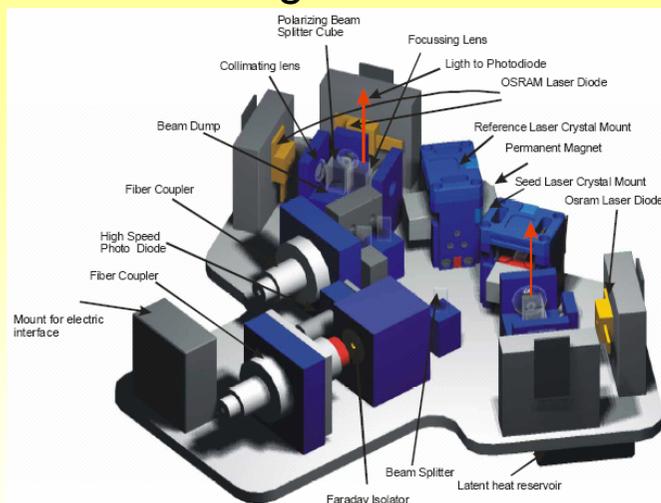
- Tripled-frequency Nd:YAG, 150 mJ at 100 Hz, operating in burst mode (7s ON 21s OFF)
- Seeded by a reference laser
- RLH Breadboard activities run by
 - Innolight
 - Tesat



Innolight RLH BB

TESAT RLH

EQM of the ALADIN transmitter



- **Aim: Identifying key parameters relevant to the Pump Laser Diodes Qualification Programme for Aeolus**

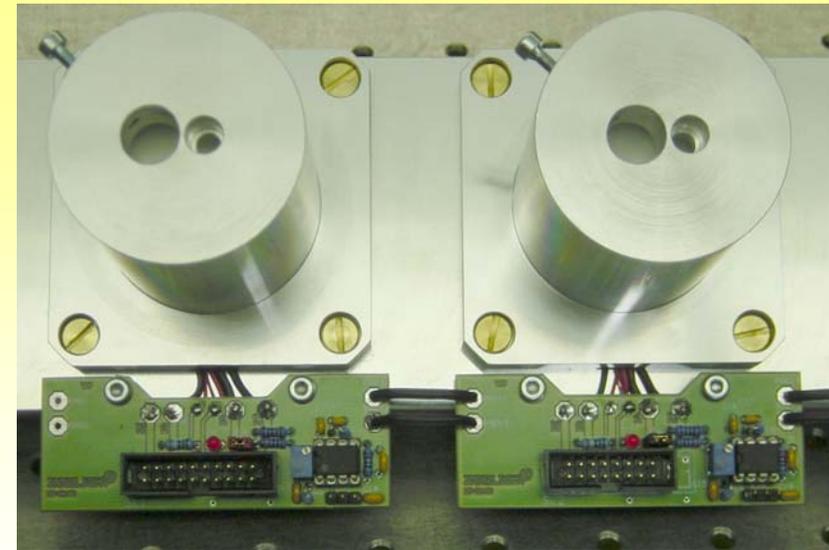
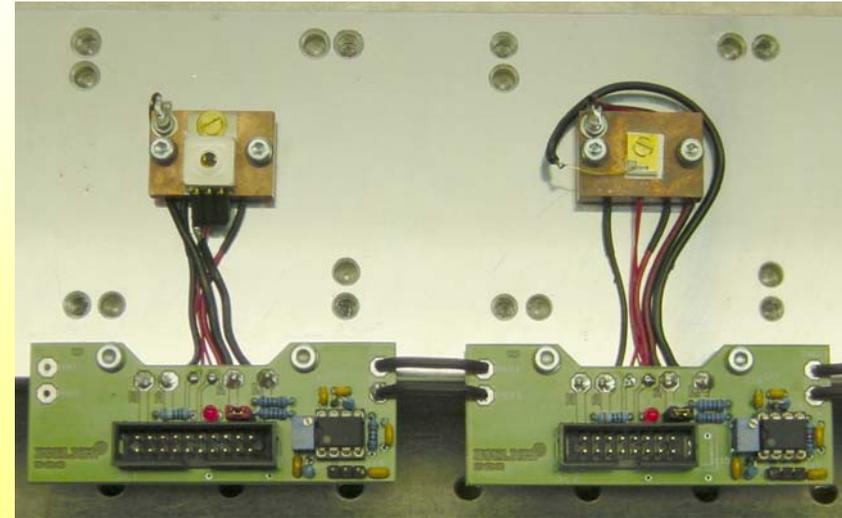
- **Tools**
 - Lifetime: 10000 h
 - Proton Irradiation tests up to $2e^{+10}$ p/cm²
 - Failure Analysis

- **Laser diodes**
 - Thales Laser Diodes (QCW)
 - Dilas (QCW)
 - Ferdinand Braun Institute (CW)
 - InnoLight: Infineon & Thales (CW)

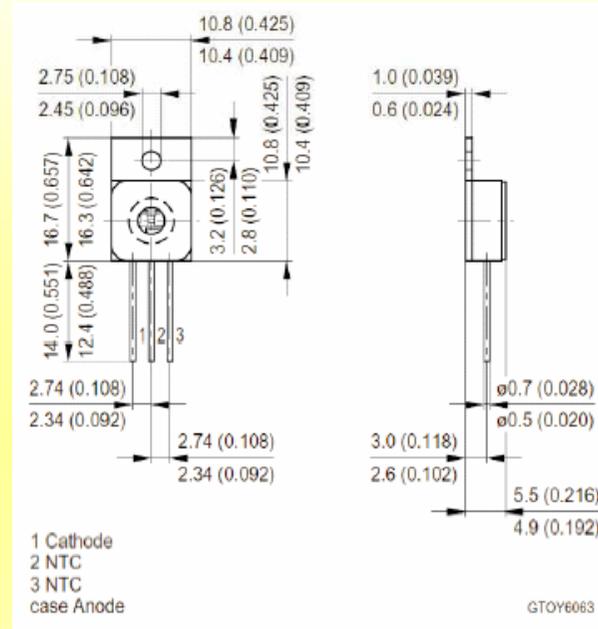




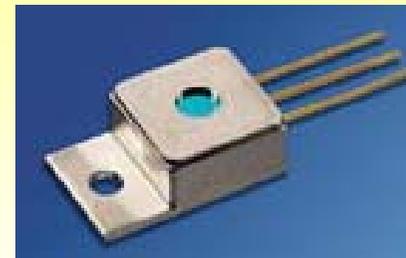
Endurance test bench setup under a class 100-1000 laminar flow box. Laser diode holder with protecting tube.



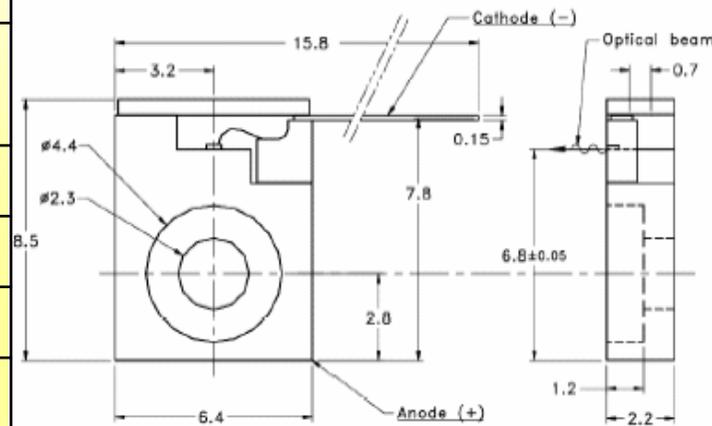
<u>Parameter</u>	<u>Typical Values</u>	<u>Units</u>
Peak wavelength	808 \pm 3	nm
Spectral width (FWHM)	3	nm
Output power	2	W
Differential efficiency	1.1	W/A
Threshold current	0.65	A
Operating current	2.5	A
Operating Voltage	2.0	V
Reverse voltage	3	V
Beam divergence (FWHM)	1.5 X 8	deg.
Thermal resistance (junction \rightarrow heat sink)	6.5	K/W
Heat-sink temperature	25	$^{\circ}$ C
Storage temperature	-40 to +85	$^{\circ}$ C



- Infineon SPL 2Y81
- Class IV Laser Product (IEC 60825-1)
- TO-220 package (copper base)
- InGa(Al)As strained layer qw structure
- Laser aperture 200 μ m
- Cylindrical correction
- Mechanical tolerances: \pm 0.2 mm



<u>Parameter</u>	<u>Typical Values</u>	<u>Units</u>
Peak wavelength	808 ± 3	nm
Spectral width (FWHM)	3	nm
Output power	1	W
Slope efficiency	1.0	W/A
Threshold current	0.4	A
Operating current	1.4	A
Operating Voltage	1.9	V
Reverse voltage	3	V
Beam divergence (FWHM)	12 X 35	deg.
Emitting area	100 x 1	µm ²
Heat-sink temperature	25	°C
Storage temperature	-40 to +85	°C



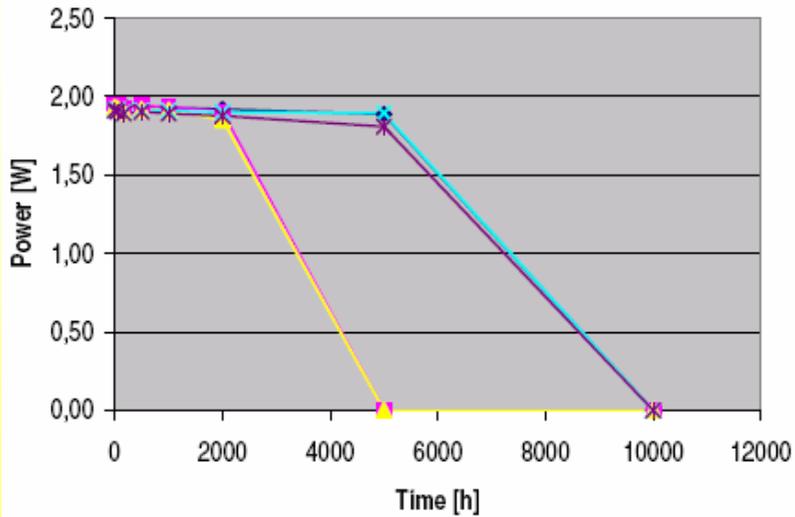
- Thales TH-C1301-E
- Class IV Laser Product (IEC 60825-1)
- Package "E" (c-mount)
- GaAlAs broad area single emitter
- Laser aperture 100 µm
- No cylindrical correction
- Mechanical tolerances: ± 0.2 mm



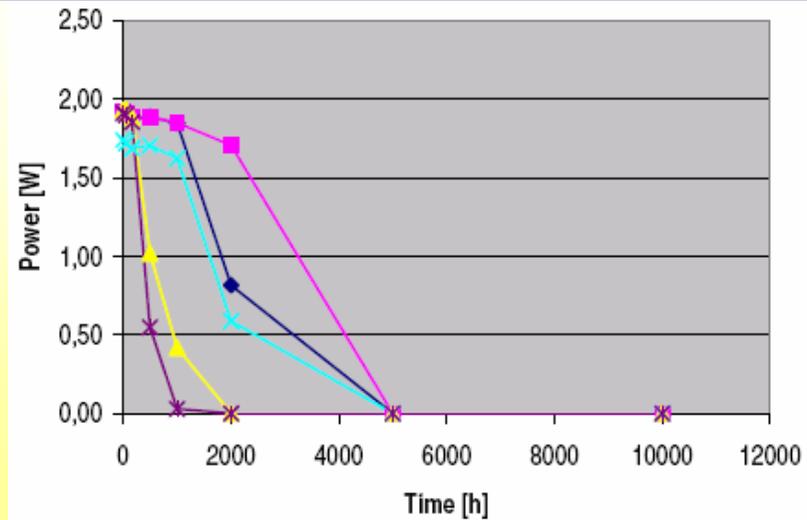
2 * 20 DL constant current for 10000 hours:

- 2 * 5: nominal current, 25 °C ± 0.5 °C case temperature
- 2 * 5: nominal current, 45 °C ± 0.5 °C case temperature
- 2 * 5: current to obtain 120% of nominal optical output power at beginning of life, temperature needed to obtain the nominal wavelength as obtained when the case temperature is 25 °C and output power is nominal.
- 2 * 5: 50 % of the nominal output power, 25 °C ± 0.5 °C case temperature

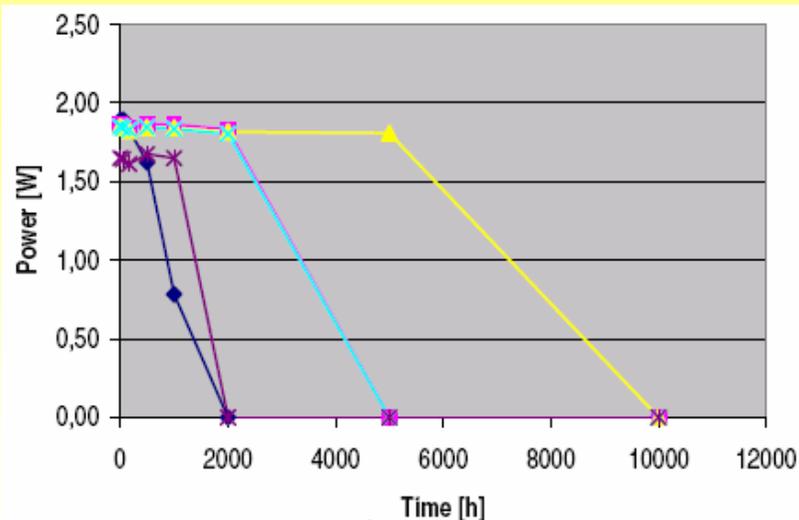
Parameter	0h	48h	168h	500h	1000h	2000h	5000h	10000h
Optical Output Power	X	X	X	X	X	X	X	X
Forward Voltage	X	X	X	X	X	X	X	X
Center Wavelength	X	X	X	X	X	X	X	X
Threshold Current	X	X	X	X	X	X	X	X
Optical Efficiency	X	X	X	X	X	X	X	X
Divergence	X			X		X	X	X
Characteristic Temperature	X			X		X	X	X
Thermal Resistance	X			X		X	X	X



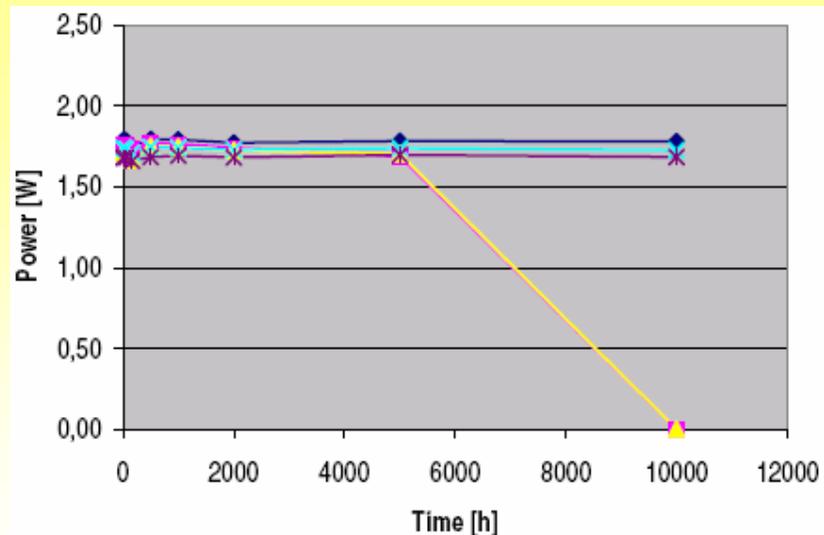
Nominal current 2.5 A, T = 25 °C



Nominal current 2.5 A, T = 45 °C



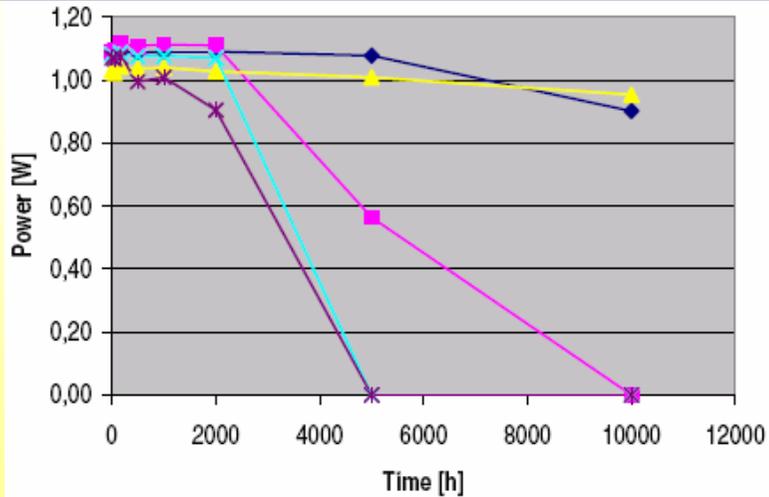
3 A, T ~ 20 °C to get nominal λ



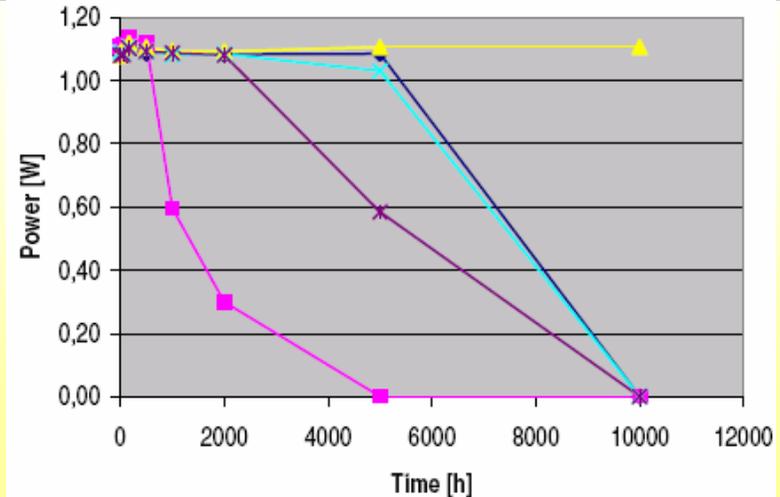
1.7 A, T = 25 °C



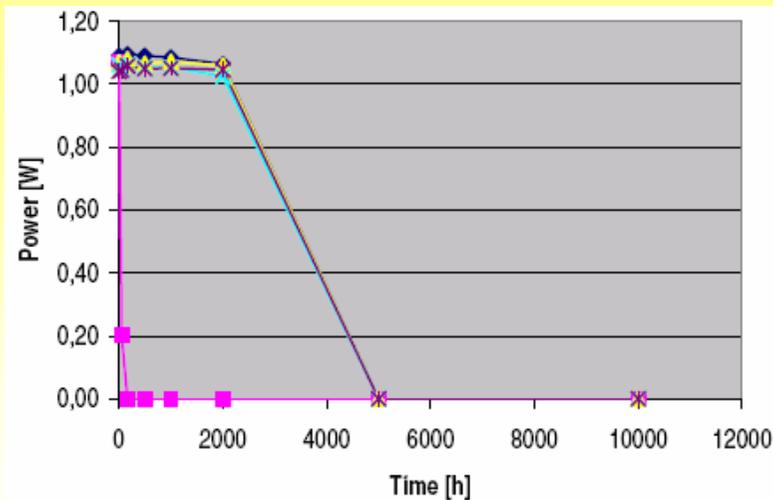
Endurance test results: Thales Laser Diodes



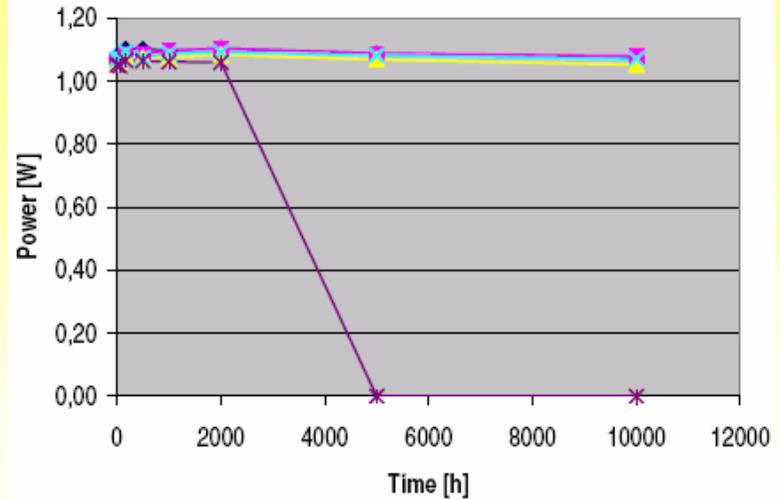
Nominal current 1.4 A, T = 25 °C



Nominal current 1.4 A, T = 45 °C



1.7 A, T ~ 22 °C to get nominal λ

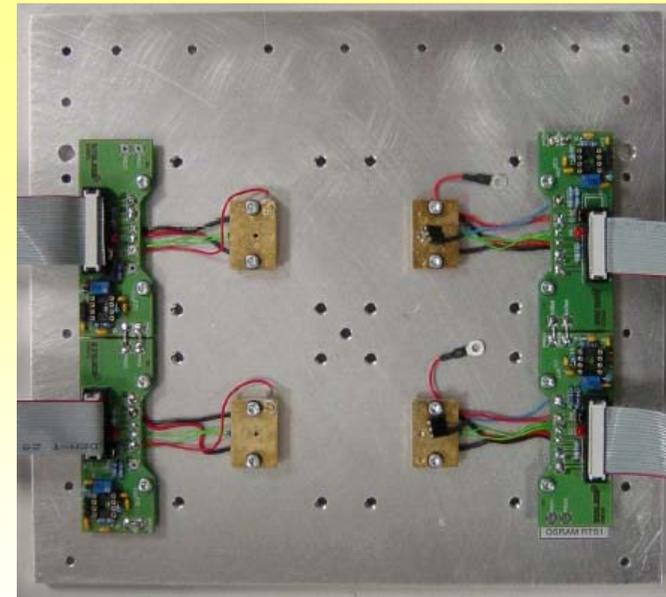
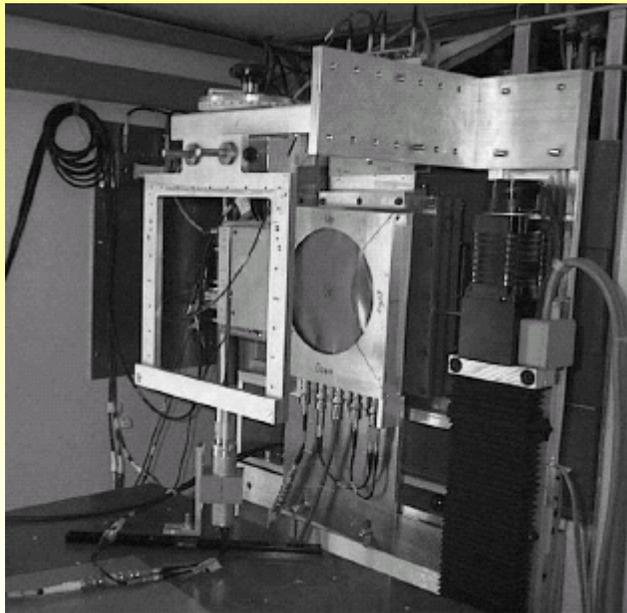


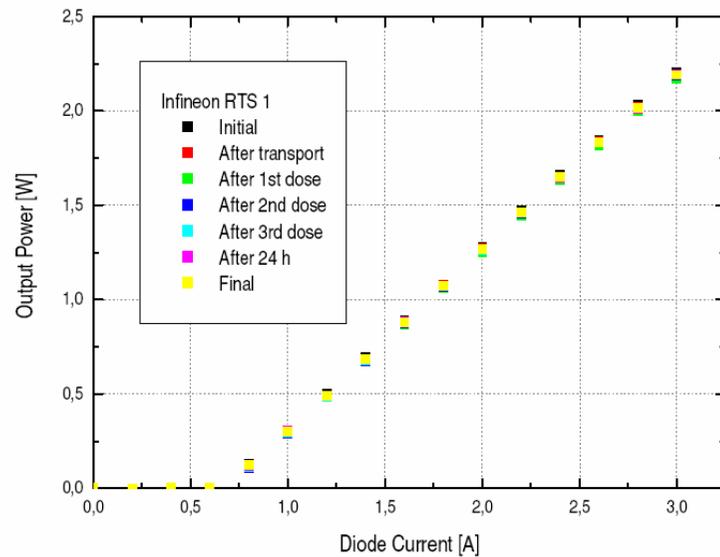
0.8 A, T = 25 °C

2 * 2 DL at $2 \cdot 10^9$ p/cm², $4 \cdot 10^9$ p/cm² and $2 \cdot 10^{10}$ p/cm²; 60MeV protons

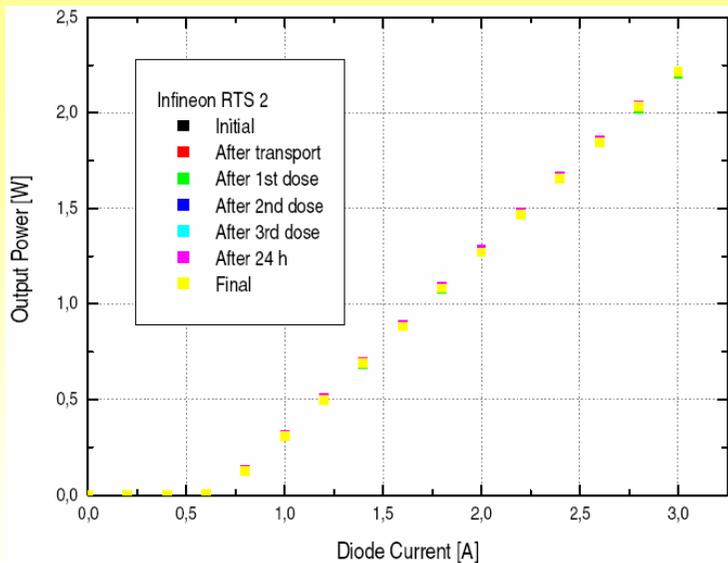
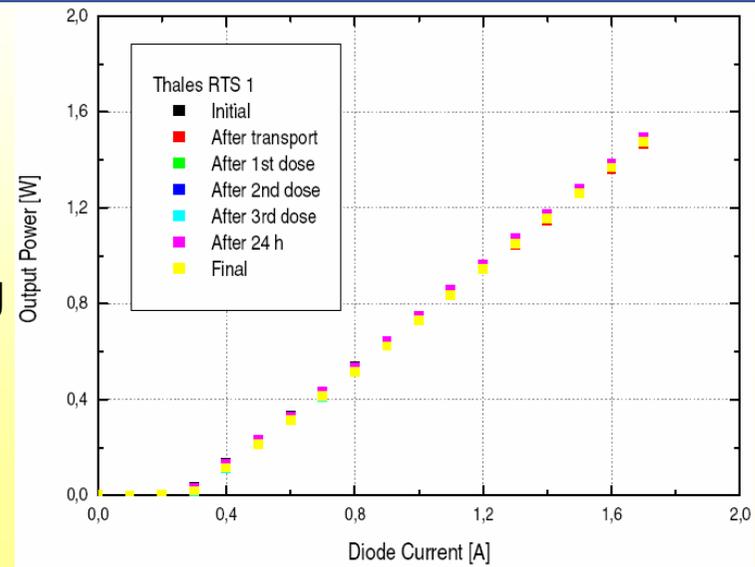
- 2 * 1: nominal operating condition
- 2 * 1: non operating condition

- Limited set of electro-optical measurement performed after each exposure level
- Full set of electro-optical measurements performed
 - 24h after last exposure level
 - after 168h annealing at 80 °C

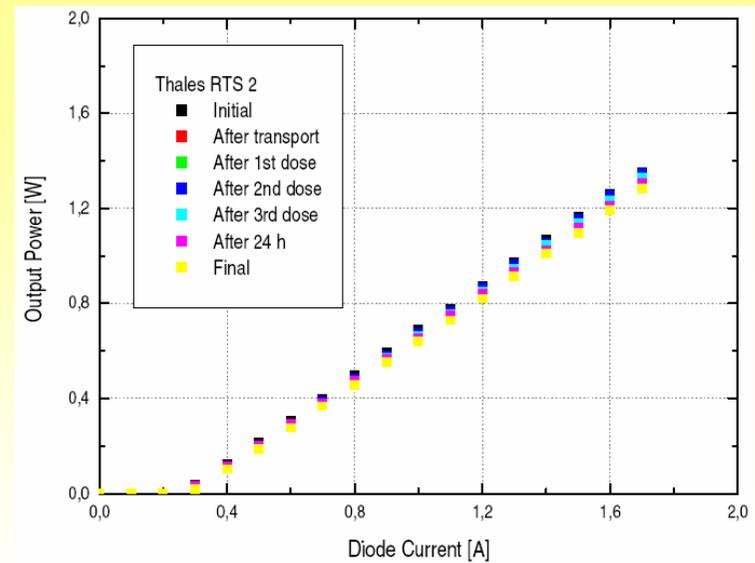


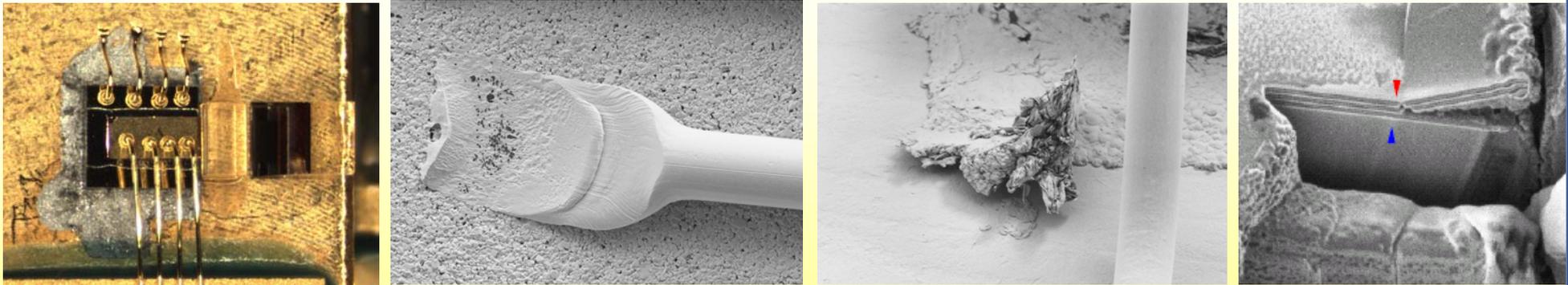


Operating



Non operating





Failure analysis performed at ESTEC:

Visual inspection

Scanning Photon Emission Microscope

LEO 1530VP Scanning Electron Microscope,

INCA EDX system installed on the SEM

Radiographic inspection

Bond strength test

Microsection with a FEI STRATA FIB 205 Focused Ion Beam System

In conclusion these analyses revealed some scratches, some minor chip-outs along laser diode edges, some fractures along the same edges and peeling/crack of the backside mirror, not acceptable soldering.



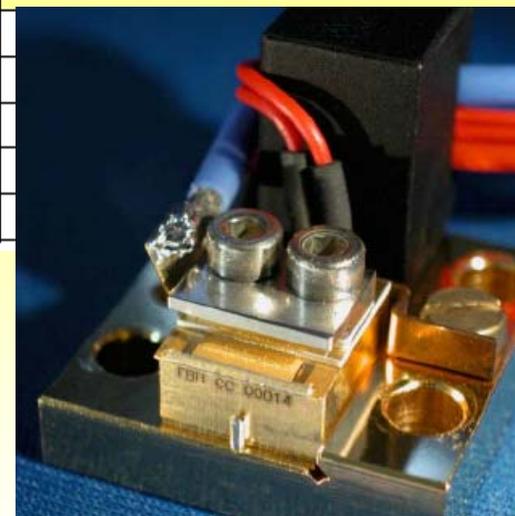
Electro-optical characterisation setup



Endurance setup : test chamber for 2 DL and test rack for the 20 DL



Parameter	Value	
Emitting area	6 emitters, 60 μm width, 1 mm pitch	
CW output power P_{op}	> 1 W	All values for $T = 25^\circ\text{C}$ and from begin of life to end of life
Operating current I	< 3.1 A	
Threshold current I_{th}	< 1.8 A	
Slope efficiency S	> 0.95 W/A	
Operating voltage U	< 1.8 V	
Life time	> 4 years	
Reliability within life time	0.98	
MTTF	1.73×10^6 h	
Wavelength λ	(807 ± 1) nm	
Spectral width $\Delta\lambda$	3 nm	
Beam divergence – fast axis	< 60°	
Beam divergence – slow axis	< 6°	



Layer structure was established and grown on a 2 " wafer

Back end process

Facet coating

Mounting on Cu carrier

Burn-in: 300 h, 5W, 70 °C

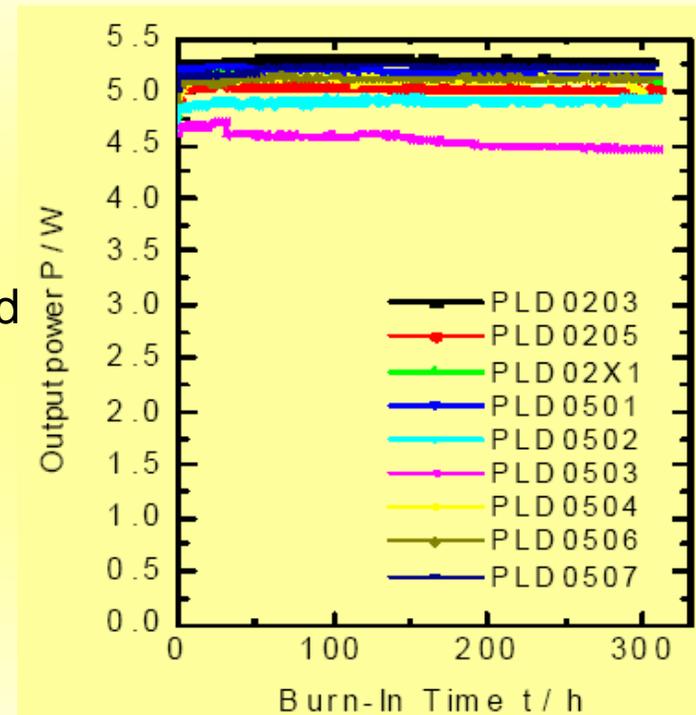
Acceptance: $DP/P < 0.01$ last 100 h → 38 bars passed

24 LD selected

20 endurance

2 radiation

2 reference



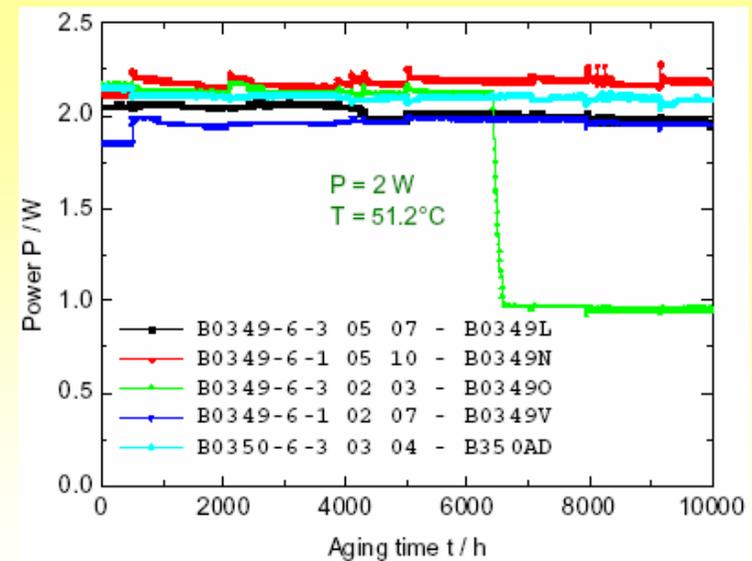
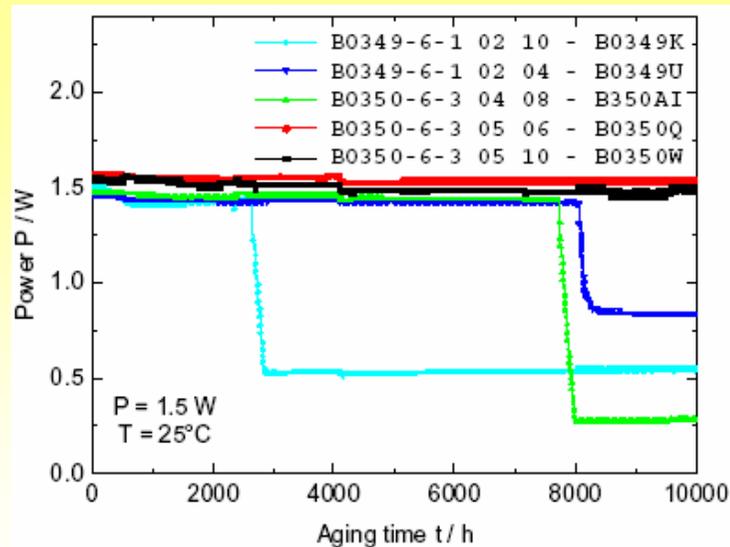
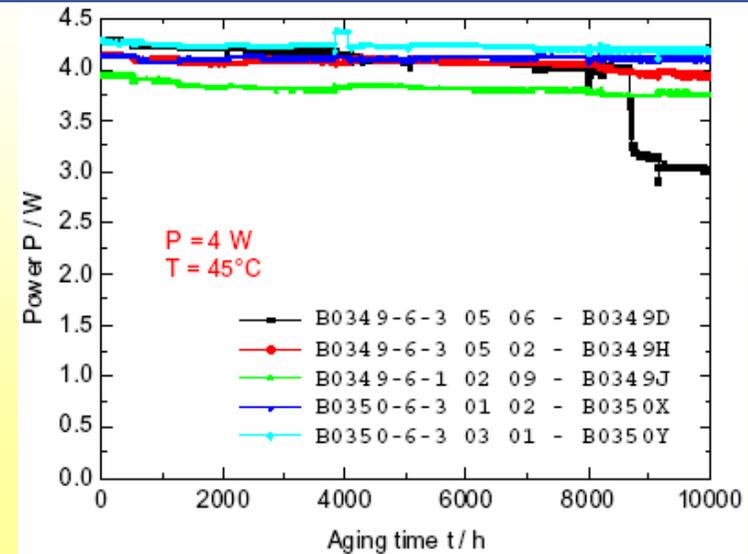
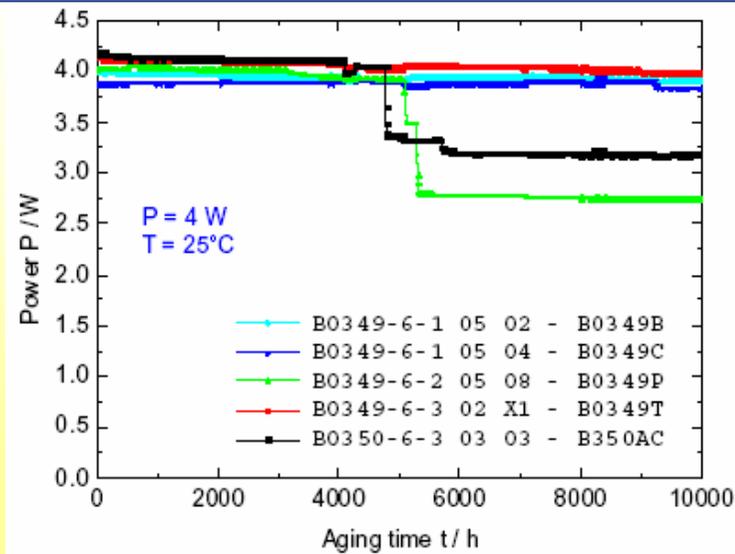
20 DL constant current for 10000 hours:

- 5: 4W, 25 °C ± 0.5 °C case temperature
- 5: 4W, 45 °C ± 0.5 °C case temperature
- 5: 2W, 51 °C ± 0.5 °C case temperature
- 5: 1.5W (nominal output power), 25 °C ± 0.5 °C case temperature

Electro-optical characterisation at 500h, 2000h and 5000h

From a reliability of 0.98 for 4 years, the MTTF value is $1.73 \cdot 10^6$, at 1W and 25 °C .
Assumption: activation energy $E_a = 0.5$ eV and power law exponent $n = 2.3$

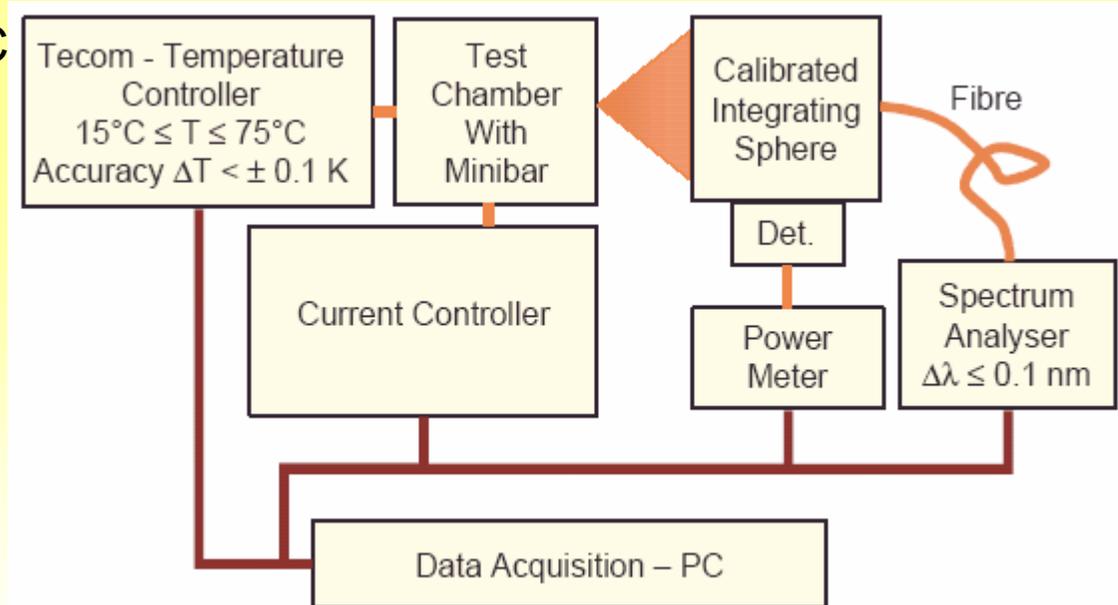
P/W	$T/°C$	Allowed Number of Failures to Proof the MTTF
4.0	25.0	0
4.0	45.0	2
1.5	25.0	-*
2.0	51.2	0

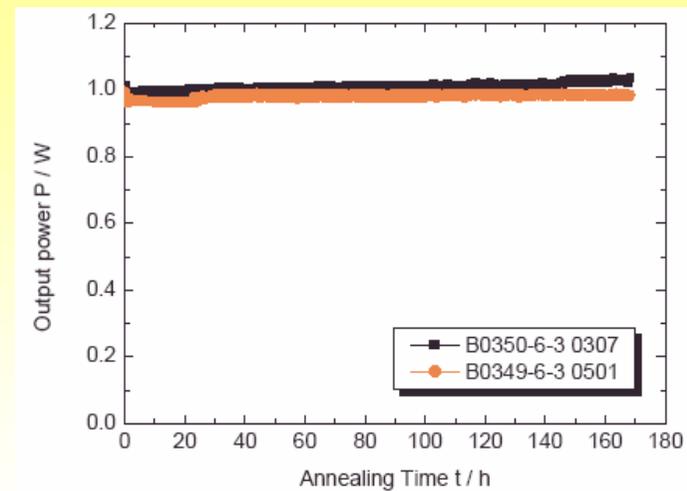
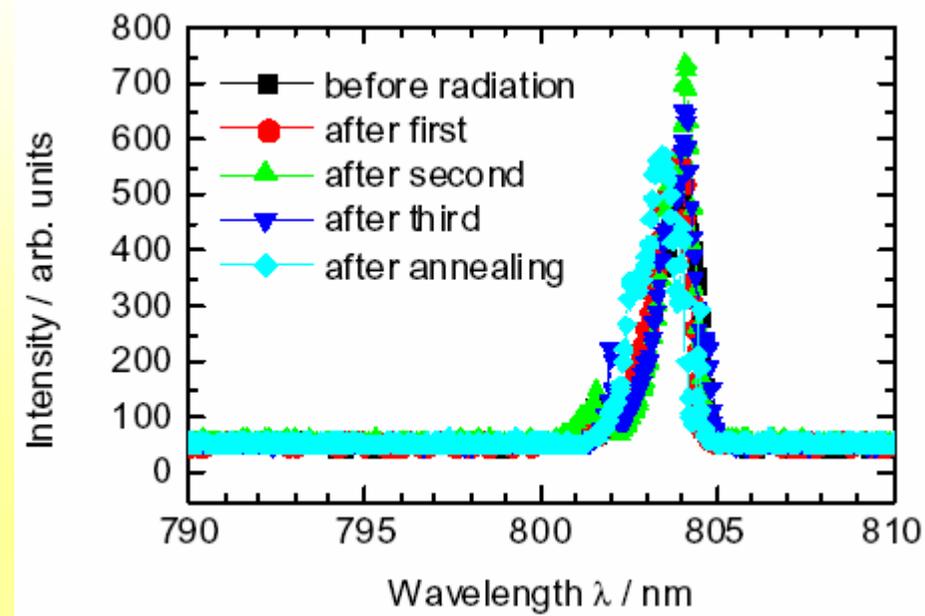
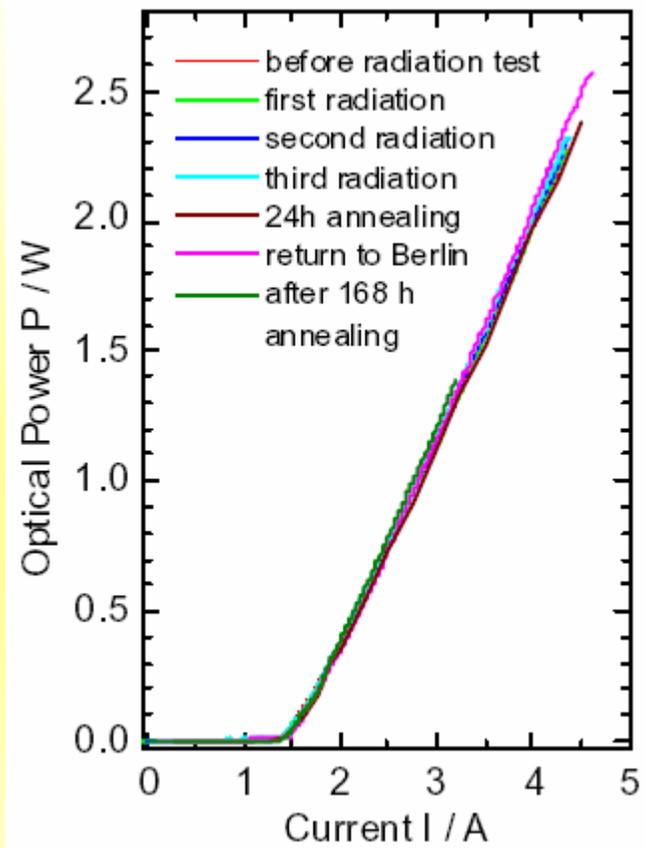


**2 DL at $2 \cdot 10^9$ p/cm², $4 \cdot 10^9$ p/cm² and $2 \cdot 10^{10}$ p/cm²;
60MeV protons 60% of rad time; 25 MeV protons 40 % of rad. time**

- 1: nominal operating condition
- 1: non operating condition

- Limited set of electro-optical measurements performed after each exposure level
- Full set of electro-optical measurements performed
 - 24h after last exposure level
 - after 168h annealing at 70 °C
- Accelerating ageing test





Anomalous failure behaviour:

- More failure at lower temperature
- No mirror defect, but electrical shunts within the diode laser bars

At lower temperature, the strain between the mounting layers is more important for larger differences between soldering and operating temperatures



Solder between heat sink and Cu mount: intermetallic compound

 **Soldering process optimised, Cu mount supplier changed
Overall strain reduced by smaller resonator length**

Radiation tests: successful for all laser diodes under the given environment (typical for LEO and 3 years lifetime)

Endurance tests: not successful, but useful:

Thales Laser Diodes: lifetime reached when derated

Osram: lifetime not met

FBH customised laser diodes: chip technology is reliable

Failure analysis:

Thales Laser Diodes-Osram: many areas to be improved (soldering, bonding, gluing...)

FBH: mounting to be improved, design to be optimised

Useful assessment test programme:

Laser diodes from FBH selected in the reference laser for ALADIN and have passed the qualification.

COTS laser diodes are less suitable for space applications than custom-designed .